

ABSTRACT

The invention provides a semiconductor device with ESD protection including a guard ring and a MOS transistor array formed in a region surrounded by the guard ring. In the invention, the MOS transistor array includes a first MOS transistor and a second MOS
5 transistor. The first MOS transistor is closer to the guard ring than the second MOS transistor is. The channel length of the second MOS transistor is greater than that of the first MOS transistor.